2.5 V / 3.3 V ECL 1:2 **Differential Fanout Buffer**

Description

The MC10/100LVEP11 is a differential 1:2 fanout buffer. The device is pin and functionally equivalent to the EP11 device. With AC performance the same as the EP11 device, the LVEP11 is ideal for applications requiring lower voltage. Single-ended CLK input operation is limited to a $V_{CC} \ge 3.0$ V in PECL mode, or $V_{EE} \le$ -3.0 V in NECL mode.

The 100 Series contains temperature compensation.

Features

- 240 ps Typical Propagation Delay
- Maximum Frequency > 3.0 GHz Typical
- PECL Mode Operating Range:
 - $V_{CC} = 2.375 \text{ V}$ to 3.8 V with $V_{EE} = 0 \text{ V}$
- NECL Mode Operating Range:
 - $V_{CC} = 0$ V with $V_{EE} = -2.375$ V to -3.8 V
- Open Input Default State
- Q Output Will Default LOW with Inputs Open or at VEE
- LVDS Input Compatible
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant



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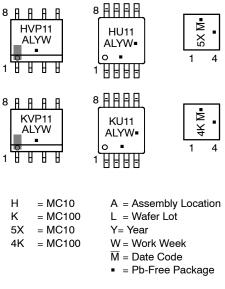
D SUFFIX CASE 751-07

DFN_8 DT SUFFIX **MN SUFFIX** 948R-02





CASE



(Note: Microdot may be in either location)

*For additional marking information, refer to Application Note AND8002/D.

ORDERING INFORMATION

See detailed ordering and shipping information on page 9 of this data sheet.

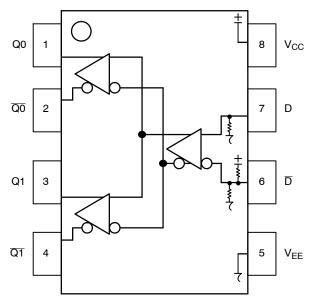


Figure 1. 8-Lead Pinout (Top View) and Logic Diagram

Table 1. PIN DESCRIPTION

PIN	FUNCTION
D*, <u>D</u> **	ECL Data Inputs
Q0, <u>Q0</u> , Q1, <u>Q1</u>	ECL Data Outputs
V _{CC}	Positive Supply
V _{EE}	Negative Supply
EP	(DFN–8 only) Thermal exposed pad must be connected to a sufficient ther- mal conduit. Electrically connect to the most negative supply (GND) or leave unconnected, floating open.

*Pins will default to 2/3 V_{CC} when left open. **Pins will default LOW when left open.

Table	2	ΔΤΤ	RIR	UTES
Table	۷.	ALL	nid	UIES

Characteristics	Value
Internal Input Pulldown Resistor	75 kΩ
Internal Input Pullup Resistor	37.5 kΩ
ESD Protection Human Body Model Machine Model Charged Device Model	> 4 kV > 200 V > 2 kV
Moisture Sensitivity, Indefinite Time Out of Drypack (Note 1)	Pb-Free Pkg
SOIC-8 NB TSSOP-8 DFN-8	Level 1 Level 3 Level 1
Flammability Rating Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in
Transistor Count	110 Devices
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test	•

1. For additional information, see Application Note <u>AND8003/D</u>.

Table 3. MAXIMUM RATINGS

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V _{CC}	PECL Mode Power Supply	V _{EE} = 0 V		6	V
V_{EE}	NECL Mode Power Supply	V _{CC} = 0 V		-6	V
VI	PECL Mode Input Voltage NECL Mode Input Voltage	V _{EE} = 0 V V _{CC} = 0 V	$\begin{array}{l} V_{I} \leq V_{CC} \\ V_{I} \geq V_{EE} \end{array}$	6 -6	V
l _{out}	Output Current	Continuous Surge		50 100	mA
T _A	Operating Temperature Range			-40 to +85	°C
T _{stg}	Storage Temperature Range			-65 to +150	°C
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	SOIC-8 NB	190 130	°C/W
θ_{JC}	Thermal Resistance (Junction-to-Case)	Standard Board	SOIC-8 NB	41 to 44	°C/W
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	TSSOP-8	185 140	°C/W
θ_{JC}	Thermal Resistance (Junction-to-Case)	Standard Board	TSSOP-8	41 to 44	°C/W
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	DFN-8	129 84	°C/W
T _{sol}	Wave Solder (Pb-Free)	<2 to 3 sec @ 260°C		265	°C
θJC	Thermal Resistance (Junction-to-Case)	(Note 1)	DFN-8	35 to 40	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1. JEDEC standard multilayer board – 2S2P (2 signal, 2 power)

			-40°C			25°C			85°C		
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Power Supply Current	25	33	40	29	33	40	32	34	42	mA
V _{OH}	Output HIGH Voltage (Note 2)	1365	1490	1615	1430	1555	1680	1490	1615	1740	mV
V _{OL}	Output LOW Voltage (Note 2)	565	740	865	630	805	930	690	865	990	mV
V _{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 3)	1.2		2.5	1.2		2.5	1.2		2.5	V
I _{IH}	Input HIGH Current			150			150			150	μA
IIL	Input LOW Current D D	0.5 -150			0.5 -150			0.5 -150			μΑ

Table 4. 10LVEP DC CHARACTERISTICS, PECL (V_{CC} = 2.5 V, V_{EE} = 0 V (Note 1))

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

1. Input and output parameters vary 1:1 with V_{CC} . V_{EE} can vary +0.125 V to -1.3 V.

2. All loading with 50 Ω to V_{CC} – 2.0 V. 3. V_{IHCMR} min varies 1:1 with V_{EE}, V_{IHCMR} max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal. Single-Ended input CLK pin operation is limited to $V_{CC} \ge 3.0$ V in PECL mode.

Table 5. 10LVEP DC CHARACTERISTICS, PECL (V_{CC} = 3.3 V, V_{FF} = 0 V (Note 1))

			-40°C			25°C			85°C		
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Power Supply Current	25	33	40	29	33	40	32	34	42	mA
V _{OH}	Output HIGH Voltage (Note 2)	2165	2290	2415	2230	2355	2480	2290	2415	2540	mV
V _{OL}	Output LOW Voltage (Note 2)	1365	1540	1665	1430	1605	1730	1490	1665	1790	mV
V _{IH}	Input HIGH Voltage (Single-Ended) (Note 3)	2090		2415	2155		2480	2215		2540	mV
V _{IL}	Input LOW Voltage (Single-Ended) (Note 3)	1365		1690	1430		1755	1490		1815	mV
V _{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 4)	1.2		3.3	1.2		3.3	1.2		3.3	V
Ι _{ΙΗ}	Input HIGH Current			150			150			150	μA
IIL	Input LOW Current D D	0.5 -150			0.5 -150			0.5 -150			μΑ

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

1. Input and output parameters vary 1:1 with V_{CC}. V_{EE} can vary +0.925 V to -0.5 V.

2. All loading with 50 Ω to V_{CC} – 2.0 V.

3. Single-Ended input CLK pin operation is limited to $V_{CC} \ge 3.0$ V in PECL mode.

4. VIHCMR min varies 1:1 with VEE, VIHCMR max varies 1:1 with VCC. The VIHCMR range is referenced to the most positive side of the differential input signal.

			−40°C			25°C			85°C		
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Power Supply Current	25	33	40	29	33	40	32	34	42	mA
V _{OH}	Output HIGH Voltage (Note 2)	-1135	-1010	-885	-1070	-945	-820	-1010	-885	-760	mV
V _{OL}	Output LOW Voltage (Note 2)	-1935	-1760	-1635	-1870	-1695	-1570	-1810	-1635	-1510	mV
V _{IH}	Input HIGH Voltage (Single-Ended) (Note 3)	-1210		-885	-1145		-820	-1085		-760	mV
V _{IL}	Input LOW Voltage (Single-Ended) (Note 3)	-1935		-1610	-1870		-1545	-1810		-1485	mV
V _{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 4)	V _{EE}	+1.2	0.0	V _{EE}	+1.2	0.0	V _{EE}	+1.2	0.0	V
I _{IH}	Input HIGH Current			150			150			150	μA
Ι _{ΙL}	Input LOW Current D D	0.5 -150			0.5 -150			0.5 -150			μA

Table 6. 10LVEP DC CHARACTERISTICS, NECL (V_{CC} = 0 V, V_{EE} = -3.8 V to -2.375 V (Note 1))

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

1. Input and output parameters vary 1:1 with $V_{\mbox{CC}}.$

2. All loading with 50 Ω to V_{CC} – 2.0 V.

3. Single-Ended input CLK pin operation is limited to $V_{EE} \leq -3.0$ V in NECL mode.

4. V_{IHCMR} min varies 1:1 with V_{EE}, V_{IHCMR} max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal.

			−40°C			25°C			85°C		
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Power Supply Current	25	35	42	29	38	46	32	41	50	mA
V _{OH}	Output HIGH Voltage (Note 2)	1355	1480	1605	1355	1480	1605	1355	1480	1605	mV
V _{OL}	Output LOW Voltage (Note 2)	555	730	900	555	730	900	555	730	900	mV
V _{IH}	Input HIGH Voltage (Single-Ended)	1335		1620	1335		1620	1335		1620	mV
V _{IL}	Input LOW Voltage (Single-Ended)	555		900	555		900	555		900	mV
VIHCMR	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 3)	1.2		2.5	1.2		2.5	1.2		2.5	V
I _{IH}	Input HIGH Current			150			150			150	μA
IIL	Input LOW Current D D	0.5 -150			0.5 -150			0.5 -150			μΑ

Table 7. 100LVEP DC CHARACTERISTICS, PECL (V_{CC} = 2.5 V, V_{EE} = 0 V (Note 1))

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

1. Input and output parameters vary 1:1 with V_{CC}. V_{EE} can vary +0.125 V to -1.3 V.

2. All loading with 50 Ω to V_{CC} – 2.0 V.

3. V_{IHCMR} min varies 1:1 with V_{EE} , V_{IHCMR} max varies 1:1 with V_{CC} . The V_{IHCMR} range is referenced to the most positive side of the differential input signal. Single-Ended input CLK pin operation is limited to $V_{CC} \ge 3.0$ V in PECL mode.

			-40°C			25°C			85°C		
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Power Supply Current	25	35	42	29	38	46	32	41	50	mA
V _{OH}	Output HIGH Voltage (Note 2)	2155	2280	2405	2155	2280	2405	2155	2280	2405	mV
V _{OL}	Output LOW Voltage (Note 2)	1355	1530	1700	1355	1530	1700	1355	1530	1700	mV
V _{IH}	Input HIGH Voltage (Single-Ended) (Note 3)	2135		2420	2135		2420	2135		2420	mV
V _{IL}	Input LOW Voltage (Single-Ended) (Note 3)	1355		1700	1355		1700	1355		1700	mV
V _{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 4)	1.2		3.3	1.2		3.3	1.2		3.3	V
I _{IH}	Input HIGH Current			150			150			150	μA
IIL	Input LOW Current D D	0.5 -150			0.5 -150			0.5 -150			μΑ

Table 8. 100LVEP DC CHARACTERISTICS, PECL (V_{CC} = 3.3 V, V_{EE} = 0 V (Note 1))

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

1. Input and output parameters vary 1:1 with V_{CC} . V_{EE} can vary +0.925 V to -0.5 V.

2. All loading with 50 Ω to V_{CC} – 2.0 V.

3. Single-Ended input CLK pin operation is limited to $V_{CC} \ge 3.0$ V in PECL mode.

4. V_{IHCMR} min varies 1:1 with V_{EE}, V_{IHCMR} max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal.

			-40°C			25°C			85°C		
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{EE}	Power Supply Current	25	35	42	29	38	46	32	41	50	mA
V _{OH}	Output HIGH Voltage (Note 2)	-1145	-1020	-895	-1145	-1020	-895	-1145	-1020	-895	mV
V _{OL}	Output LOW Voltage (Note 2)	-1945	-1770	-1600	-1945	-1770	-1600	-1945	-1770	-1600	mV
V _{IH}	Input HIGH Voltage (Single-Ended) (Note 3)	-1165		-880	-1165		-880	-1165		-880	mV
V _{IL}	Input LOW Voltage (Single-Ended) (Note 3)	-1945	-1425	-1600	-1945	-1425	-1600	-1945	-1425	-1600	mV
V _{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 4)	V _{EE}	+1.2	0.0	V _{EE}	+1.2	0.0	V _{EE}	+1.2	0.0	V
I _{IH}	Input HIGH Current			150			150			150	μA
IIL	Input LOW Current D D	0.5 -150			0.5 -150			0.5 -150			μΑ

Table 9. 100LVEP DC CHARACTERISTICS, NECL (V_{CC} = 0 V; V_{EE} = -3.8 V to -2.375 V (Note 1))

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

1. Input and output parameters vary 1:1 with V_{CC} .

2. All loading with 50 Ω to V_{CC} – 2.0 V.

3. Single-Ended input CLK pin operation is limited to V_{EE} ≤ -3.0 V in NECL mode.

4. V_{IHCMR} min varies 1:1 with V_{EE}, V_{IHCMR} max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal.

				–40°C			25°C			85°C		
Symbol	Characteristic		Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Uni
f _{max}	Maximum Frequency (Figure 2)			3			3			3		GH:
t _{PLH} , t _{PHL}	Propagation Delay (Differential Configuration) CLK to Q, Q		170	230	300	180	240	310	210	270	360	ps
t _{SKEW}	Within Device Skew Device to Device Skew (Note 2)	Q,		5.0	20 130		5.0	20 130		5.0	20 150	ps
t _{JITTER}	CLOCK Random Jitter (RMS) @ ≤1.0 GHz @ ≤1.5 GHz @ ≤2.0 GHz @ ≤2.5 GHz @ ≤3.0 GHz			0.126 0.112 0.111 0.112 0.155	0.3 0.2 0.3 0.2 0.2		0.142 0.162 0.122 0.172 0.217	0.4 0.3 0.2 0.3 0.3		0.209 0.162 0.170 0.235 0.368	0.3 0.2 0.3 0.3 0.6	ps
V_{PP}	Input Voltage Swing (Differential Configuration)		150	800	1200	150	800	1200	150	800	1200	mV
t _r t _f	Output Rise/Fall Times (20% – 80%)	Q,	70	110	170	80	120	180	100	140	200	ps

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

1. Measured using a 750 mV source, 50% duty cycle clock source. All loading with 50 Ω to V_{CC} – 2.0 V.

2. Skew is measured between outputs under identical transitions.

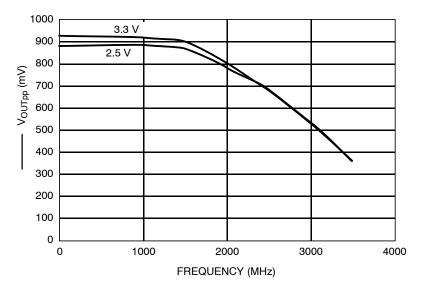
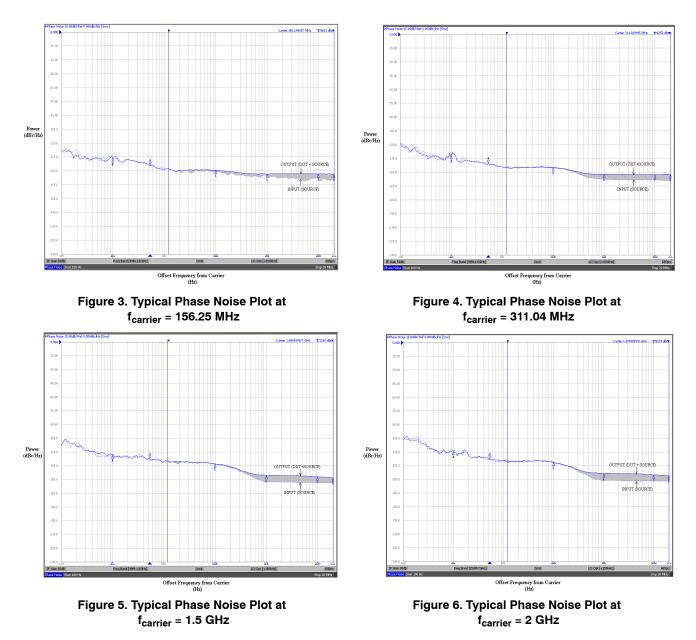


Figure 2. F_{max} Typical



The above phase noise plots captured using Agilent E5052A show additive phase noise of the MC100LVEP11 device at frequencies 156.25 MHz, 311.04 MHz, 1.5 GHz and 2 GHz respectively at an operating voltage of 3.3 V in room temperature. The RMS Phase Jitter contributed by the

device (integrated between 12 kHz and 20 MHz; as shown in the shaded region of the plot) at each of the frequencies is 66 fs, 37 fs, 14 fs and 13 fs respectively. The input source used for the phase noise measurements is Agilent E8663B.

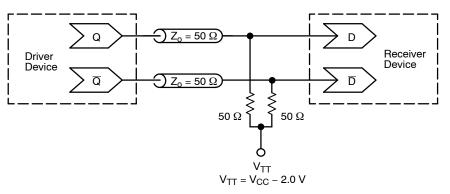


Figure 7. Typical Termination for Output Driver and Device Evaluation (See Application Note <u>AND8020/D</u> – Termination of ECL Logic Devices.)

ORDERING INFORMATION

Device	Package	Shipping [†]
MC10LVEP11DG	SOIC-8 NB (Pb-Free)	98 Units / Rail
MC10LVEP11DR2G	SOIC-8 NB (Pb-Free)	2500 / Tape & Reel
MC10LVEP11DTG	TSSOP–8 (Pb-Free)	100 Units / Rail
MC10LVEP11DTR2G	TSSOP–8 (Pb-Free)	2500 / Tape & Reel
MC100LVEP11DG	SOIC-8 (Pb-Free)	98 Units / Rail
MC100LVEP11DR2G	SOIC-8 (Pb-Free)	2500 / Tape & Reel
MC100LVEP11DTG	TSSOP–8 (Pb-Free)	100 Units / Rail
MC100LVEP11DTR2G	TSSOP–8 (Pb-Free)	2500 / Tape & Reel
MC100LVEP11MNR4G	DFN-8 (Pb-Free)	1000 / Tape & Reel

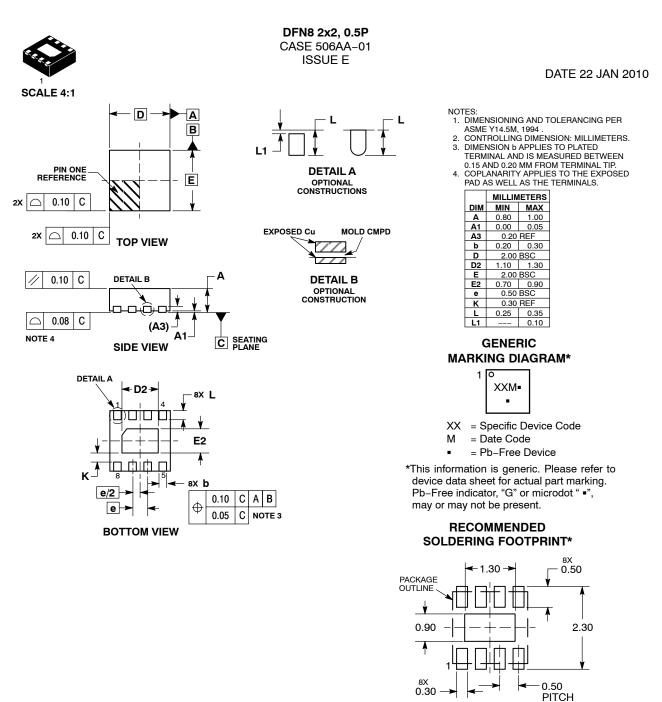
+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, <u>BRD8011/D</u>.

Resource Reference of Application Notes

AN1405/D	-	ECL Clock Distribution Techniques	
AN1406/D	-	Designing with PECL (ECL at +5.0 V)	
AN1503/D	-	ECLinPS [™] I/O SPiCE Modeling Kit	
AN1504/D	-	Metastability and the ECLinPS Family	
AN1568/D	-	Interfacing Between LVDS and ECL	
AN1672/D	-	The ECL Translator Guide	
AND8001/D	-	Odd Number Counters Design	
AND8002/D	-	Marking and Date Codes	
AND8020/D	-	Termination of ECL Logic Devices	
AND8066/D	-	Interfacing with ECLinPS	
AND8090/D	_	AC Characteristics of ECL Devices	

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*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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SOIC-8 NB CASE 751-07 **ISSUE AK**

STYLE 1: PIN 1. EMITTER COLLECTOR 2. COLLECTOR З. 4. EMITTER EMITTER 5. BASE 6. 7 BASE 8. EMITTER STYLE 5: PIN 1. DRAIN 2. DRAIN З. DRAIN DRAIN 4. 5. GATE 6. GATE SOURCE 7. 8. SOURCE STYLE 9: PIN 1. EMITTER, COMMON COLLECTOR, DIE #1 COLLECTOR, DIE #2 2. З. EMITTER, COMMON 4. 5. EMITTER, COMMON 6. BASE, DIE #2 BASE, DIE #1 7. 8. EMITTER, COMMON STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 17: PIN 1. VCC 2. V2OUT V10UT З. 4. TXE 5. RXE 6. VFF GND 7. 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 З. CATHODE 3 CATHODE 4 4. 5. CATHODE 5 6. COMMON ANODE COMMON ANODE 7. 8. CATHODE 6 STYLE 25: PIN 1. VIN 2 N/C З. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT STYLE 29: BASE, DIE #1 PIN 1. EMITTER, #1 BASE, #2 2. З. EMITTER, #2 4. 5 COLLECTOR, #2 COLLECTOR, #2 6.

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 COLLECTOR, #2 З. 4 COLLECTOR, #2 BASE, #2 5. EMITTER, #2 6. 7 BASE #1 EMITTER, #1 8. STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN SOURCE 4. SOURCE 5. 6. GATE GATE 7. 8. SOURCE STYLE 10: PIN 1. GROUND BIAS 1 OUTPUT 2. З. GROUND 4. 5. GROUND BIAS 2 INPUT 6. 7. 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE P-SOURCE 3 P-GATE 4. 5. P-DRAIN 6. P-DRAIN N-DRAIN 7. 8. N-DRAIN STYLE 18: PIN 1. ANODE 2. ANODE SOURCE 3. GATE 4. 5. DRAIN 6 DRAIN CATHODE 7. 8. CATHODE STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3 COMMON CATHODE/VCC I/O LINE 3 4. 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND STYLE 26: PIN 1. GND 2 dv/dt ENABLE З. 4. ILIMIT 5. SOURCE SOURCE 6. SOURCE 7. 8. VCC STYLE 30: PIN 1. DRAIN 1 DRAIN 1 2 GATE 2 З. SOURCE 2 4. SOURCE 1/DRAIN 2 SOURCE 1/DRAIN 2 5. 6.

STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1
STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd
STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 7. DRAIN 1 8. DRAIN 1
STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON
STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1
STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT
STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN

DATE 16 FEB 2011

STYLE 4: ANODE ANODE PIN 1. 2. ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 BASE, #2 З. COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE SOURCE SOURCE 2. 3. 4. GATE 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 EMITTER, DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE 2. EMITTER З. COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE CATHODE COLLECTOR/ANODE 6. 7. COLLECTOR/ANODE 8. STYLE 28: PIN 1. SW_TO_GND 2. DASIC OFF DASIC_SW_DET 3. 4. GND 5. 6. V MON VBULK 7. VBULK 8. VIN

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SOURCE 1/DRAIN 2

7.

8. GATE 1

7.

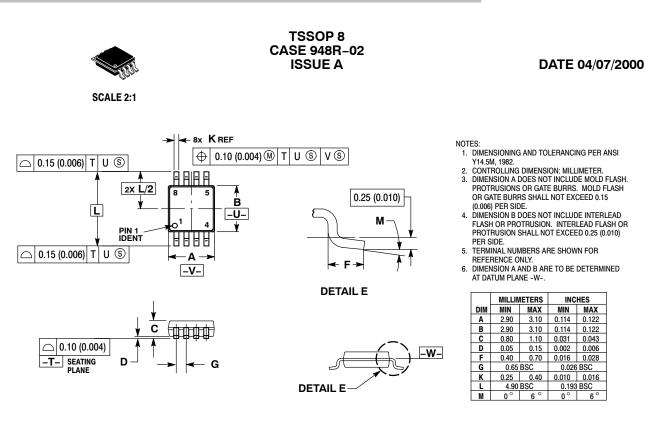
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COLLECTOR, #1

COLLECTOR, #1





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